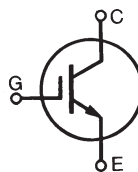


High Voltage IGBT

IXGH 32N170
IXGT 32N170

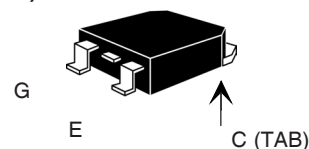
V_{CES} = 1700 V
I_{C25} = 75 A
V_{CE(sat)} = 3.3 V
t_{fi(typ)} = 250 ns

Preliminary Data Sheet

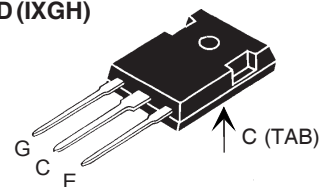


Symbol	Test Conditions	Maximum Ratings	
V _{CES}	T _J = 25°C to 150°C	1700	V
V _{CGR}	T _J = 25°C to 150°C; R _{GE} = 1 MΩ	1700	V
V _{GES}	Continuous	±20	V
V _{GEM}	Transient	±30	V
I _{C25}	T _C = 25°C	75	A
I _{C90}	T _C = 90°C	32	A
I _{CM}	T _C = 25°C, 1 ms	200	A
SSOA (RBSOA)	V _{GE} = 15 V, T _{VJ} = 125°C, R _G = 5 Ω Clamped inductive load	I _{CM} = 90 @ 0.8 V _{CES}	A
P _C	T _C = 25°C	350	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
Maximum Lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
Maximum Tab temperature for soldering SMD devices for 10 s		260	°C
M _d	Mounting torque (M3)	1.13/10Nm/lb.in.	
Weight		TO-247 AD	6 g
		TO-268	4 g

TO-268 (IXGT)



TO-247 AD (IXGH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard packages JEDEC TO-268 and JEDEC TO-247 AD
- High current handling capability
- MOS Gate turn-on - drive simplicity
- Rugged NPT structure
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- Capacitor discharge & pulser circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

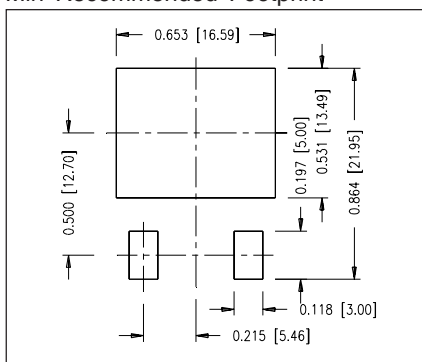
Advantages

- High power density
- Suitable for surface mounting
- Easy to mount with 1 screw, (isolated mounting screw hole)

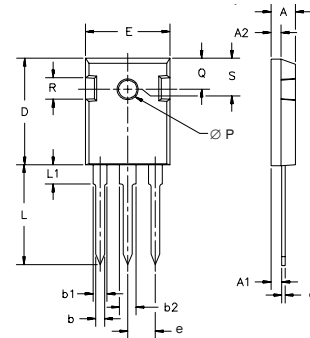
Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	I _C = 250 μA, V _{GE} = 0 V	1700		V
V_{GE(th)}	I _C = 250 μA, V _{CE} = V _{GE}	3.0		V
I_{CES}	V _{CE} = 0.8 • V _{CES} V _{GE} = 0 V			50 μA 1 mA
I_{GES}	V _{CE} = 0 V, V _{GE} = ±20 V			±100 nA
V_{CE(sat)}	I _C = I _{C90} , V _{GE} = 15 V			2.5 V 3.0 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$	22	30	S
$I_{C(ON)}$	$V_{GE} = 10\text{ V}$, $V_{CE} = 10\text{ V}$		120	A
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		3500	pF
C_{oes}			165	pF
C_{res}			40	pF
Q_g	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		155	nC
Q_{ge}			30	nC
Q_{gc}			51	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 0.6 V_{CES}$, $R_G = R_{off} = 2.7\ \Omega$		45	ns
t_{ri}			38	ns
$t_{d(off)}$			270	500 ns
t_{fi}			250	500 ns
E_{off}			11	20 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 0.6 V_{CES}$, $R_G = R_{off} = 2.7\ \Omega$		48	ns
t_{ri}			42	ns
E_{on}			6.0	mJ
$t_{d(off)}$			360	ns
t_{fi}			560	ns
E_{off}			14	mJ
R_{thJC}			0.35	KW
R_{thCK}	(TO-247)	0.25		KW

Min Recommended Footprint

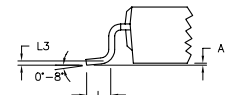
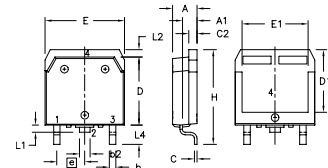


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L ₁	1.20	1.40	.047	.055
L ₂	1.00	1.15	.039	.045
L ₃		0.25		.010
L ₄	3.80	4.10	.150	.161

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343 6,583,505

Fig. 1. Output Characteristics @ 25 Deg. C

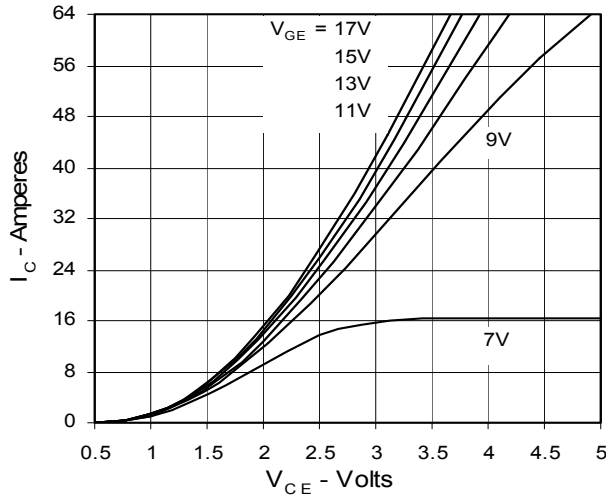


Fig. 2. Extended Output Characteristics @ 25 deg. C

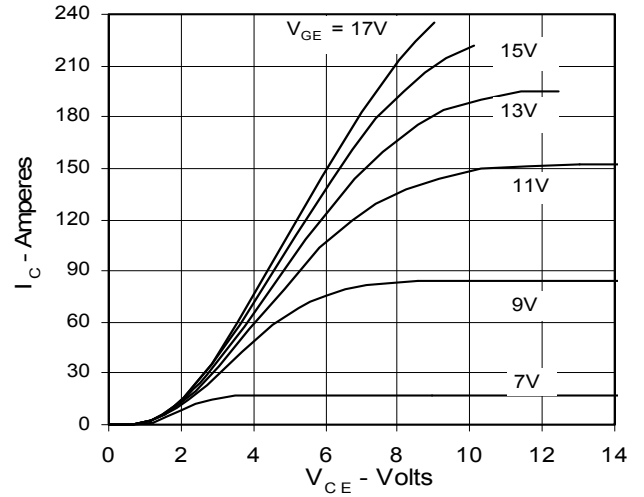


Fig. 3. Output Characteristics @ 125 Deg. C

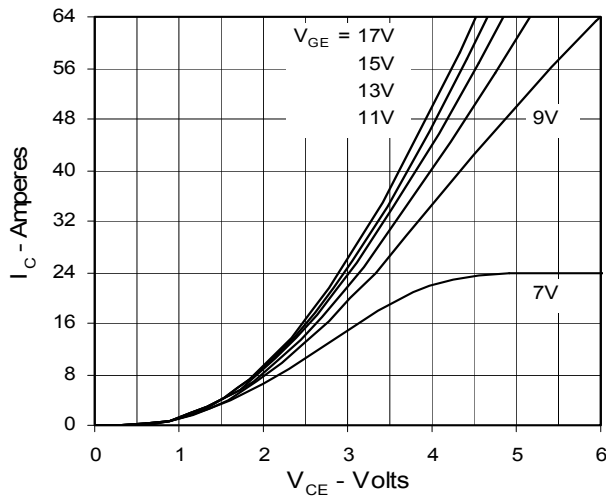


Fig. 4. Dependence of $V_{CE(sat)}$ on Temperature

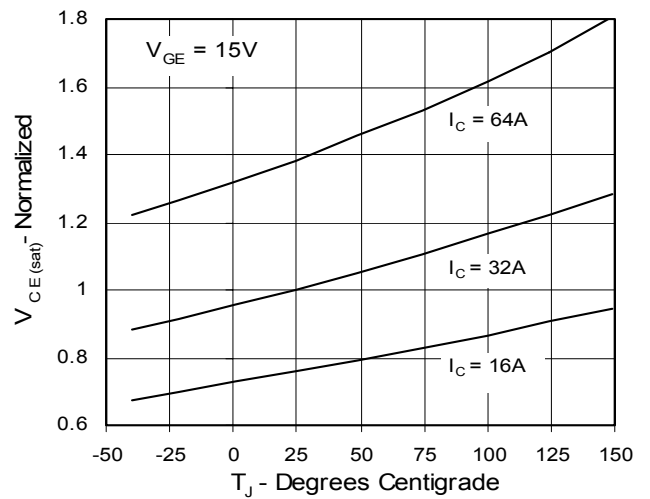


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter voltage

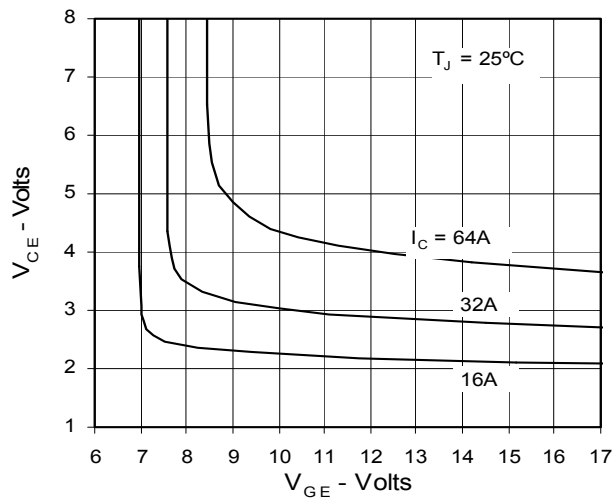


Fig. 6. Input Admittance

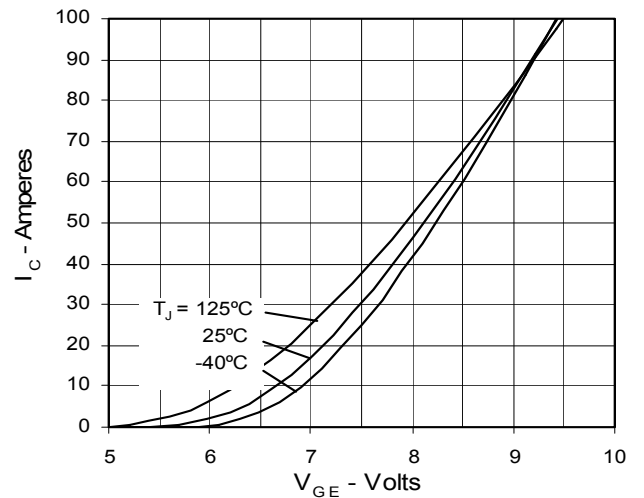


Fig. 7. Transconductance

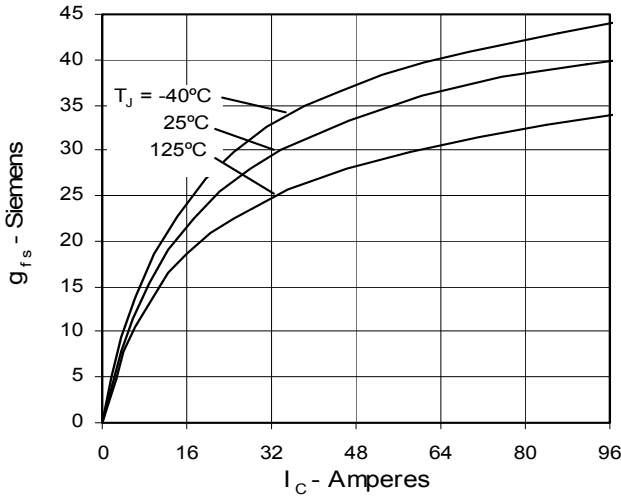


Fig. 8. Dependence of E_{off} on R_G

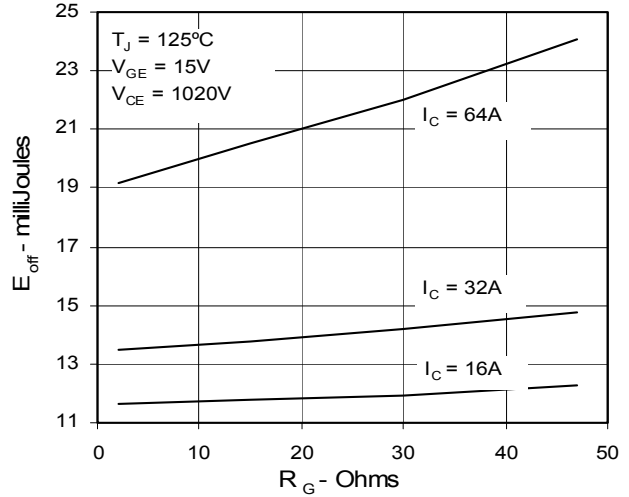


Fig. 9. Dependence of E_{off} on I_C

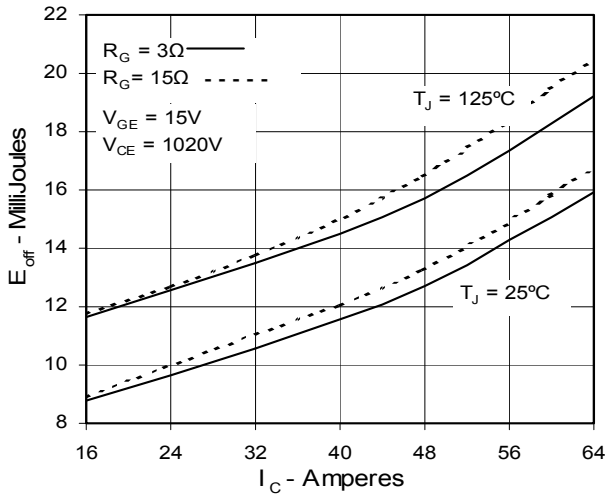


Fig. 10. Dependence of E_{off} on Temperature

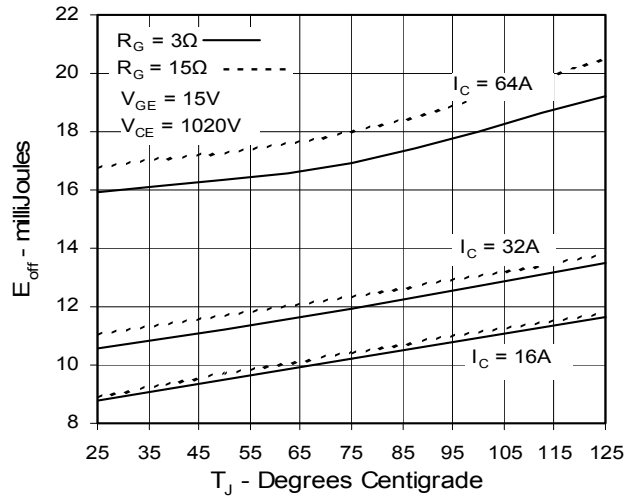


Fig. 11. Gate Charge

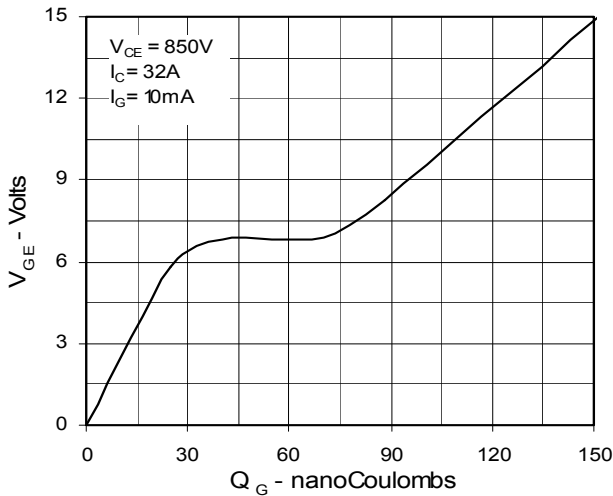
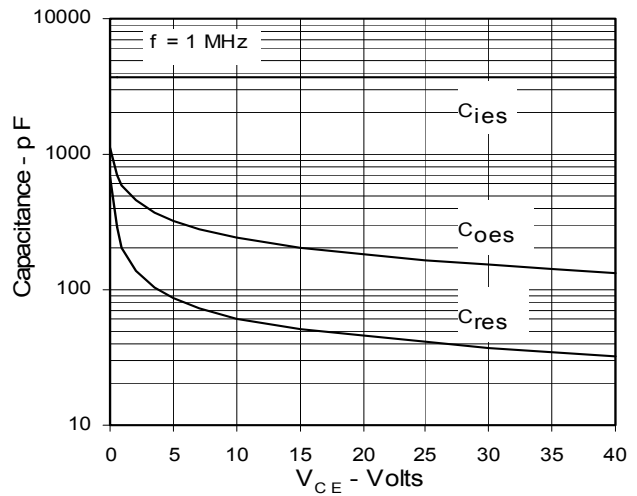


Fig. 12. Capacitance



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Fig. 13. Maximum Transient Thermal Resistance

